

# TLP130

Programmable Controllers  
 AC / DC-Input Module  
 Telecommunication

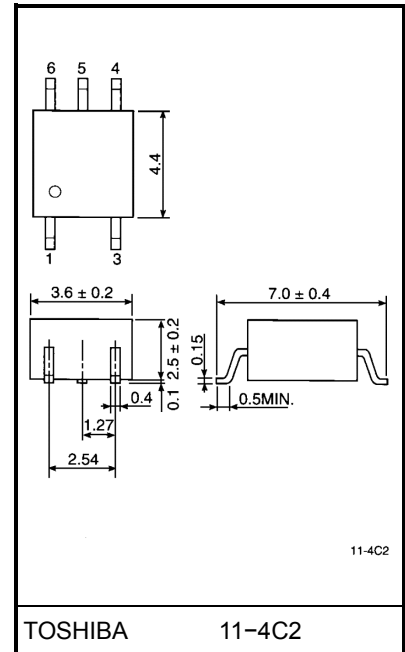
The TOSHIBA mini flat coupler TLP130 is a small outline coupler, suitable for surface mount assembly. TLP130 consists of a photo transistor, optically coupled to two gallium arsenide infrared emitting diode connected inverse parallel, and operate directly by AC input current.

- Collector-emitter voltage: 80V(min.)
- Current transfer ratio: 50%(min.)  
     Rank GB: 100%(min.)
- Isolation voltage: 3750Vrms(min.)
- UL recognized: UL1577, file no.E67349
- Current transfer ratio

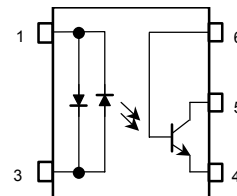
Classi- fication	Current Transfer Ratio		Marking Of Classification
	$I_F = 5\text{mA}, V_{CE} = 5\text{V}, T_a = 25^\circ\text{C}$		
	Min.	Max.	
Standard	50	600	Blank, Y, GR, GB
Rank GB	100	600	GB,GR

(Note) Application type name for certification test,  
 please use standard product type name, i.e.  
 TLP130(GB): TLP130

Unit in mm



Weight: 0.09 g



- 1 : Anode, Cathode
- 3 : Cathode, Anode
- 4 : Emitter
- 5 : Collector
- 6 : Base

## Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	$I_{F(RMS)}$	50	mA
	Forward current derating (Ta≥53°C)	$\Delta I_F / ^\circ C$	-0.7	mA / °C
	Peak forward current (100μs pulse, 100pps)	$I_{FP}$	1	A
	Junction temperature	$T_j$	125	°C
Detector	Collector-emitter voltage	$V_{CEO}$	80	V
	Collector-base voltage	$V_{CBO}$	80	V
	Emitter-collector voltage	$V_{ECO}$	7	V
	Emitter-base voltage	$V_{EBO}$	7	V
	Collector current	$I_C$	50	mA
	Peak collector current (10ms pulse, 100pps)	$I_{CP}$	100	mA
	Power dissipation	$P_C$	150	mW
	Power dissipation derating (Ta≥25°C)	$\Delta P_C / ^\circ C$	-1.5	mW / °C
	Junction temperature	$T_j$	125	°C
Storage temperature range		$T_{stg}$	-55~125	°C
Operating temperature range		$T_{opr}$	-55~100	°C
Lead soldering temperature (10s)		$T_{sol}$	260	°C
Total package power dissipation		$P_T$	200	mW
Total package power dissipation derating (Ta≥25°C)		$\Delta P_T / ^\circ C$	-2.0	mW / °C
Isolation voltage (AC, 1min., RH ≤ 60%) (Note 1)		$BV_S$	3750	Vrms

(Note 1) Device considered a two terminal device: Pins 1 and 3 shorted together and pins 4, 5 and 6 shorted together.

## Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	$V_{CC}$	—	5	48	V
Forward current	$I_{F(RMS)}$	—	16	25	mA
Collector current	$I_C$	—	1	10	mA
Operating temperature	$T_{opr}$	-25	—	85	°C

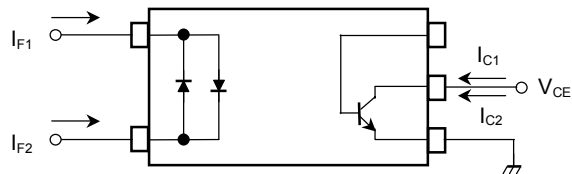
## Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	$V_F$	$I_F = \pm 10\text{mA}$	1.0	1.15	1.3	V
	Capacitance	$C_T$	$V = 0, f = 1\text{MHz}$	—	60	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	80	—	—	V
	Emitter-collector breakdown voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.1\text{mA}$	80	—	—	V
	Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector dark current	$I_{CEO}$	$V_{CE} = 48\text{V}$	—	10	100	nA
			$V_{CE} = 48\text{V}, T_a = 85^\circ\text{C}$	—	2	50	$\mu\text{A}$
	Collector dark current	$I_{CER}$	$V_{CE} = 48\text{V}, T_a = 85^\circ\text{C}$ $R_{BE} = 1\text{M}\Omega$	—	0.5	10	$\mu\text{A}$
	Collector dark current	$I_{CBO}$	$V_{CB} = 10\text{V}$	—	0.1	—	nA
	DC forward current gain	$h_{FE}$	$V_{CE} = 5\text{V}, I_C = 0.5\text{mA}$	—	400	—	—
	Capacitance collector to emitter	$C_{CE}$	$V = 0, f = 1\text{MHz}$	—	10	—	pF

## Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	$I_C / I_F$	$I_F = \pm 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_{F(sat)}$	$I_F = \pm 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Base photo-current	$I_{PB}$	$I_F = \pm 5\text{mA}, V_{CB} = 5\text{V}$	—	10	—	$\mu\text{A}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2.4\text{mA}, I_F = \pm 8\text{mA}$ $I_C = 0.2\text{mA}, I_F = \pm 1\text{mA}$ Rank GB	—	—	0.4	V
			—	0.2	—	
			—	—	0.4	
Off-state collector current	$I_{C(off)}$	$I_F = \pm 0.7\text{mA}, V_{CE} = 48\text{V}$	—	1	10	$\mu\text{A}$
CTR symmetry	$I_{C(ratio)}$	$I_C(I_F = -5\text{mA}) / I_C(I_F = 5\text{mA})$ (Note 2)	0.33	—	3	—

(Note 2)  $I_{C(ratio)} = \frac{I_{C2}(I_F = I_{F2}, V_{CE} = 5\text{V})}{I_{C1}(I_F = I_{F1}, V_{CE} = 5\text{V})}$



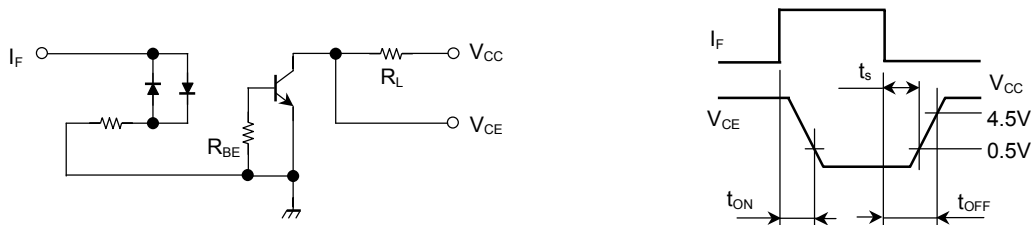
## Isolation Characteristics (Ta = 25°C)

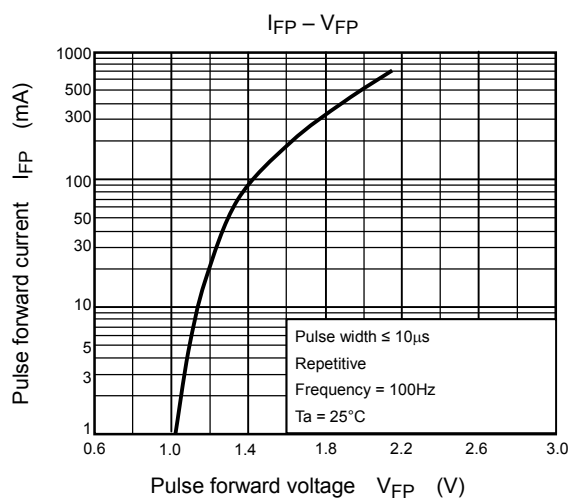
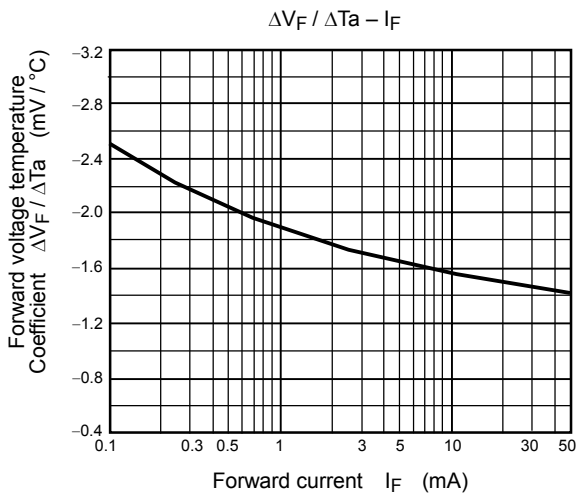
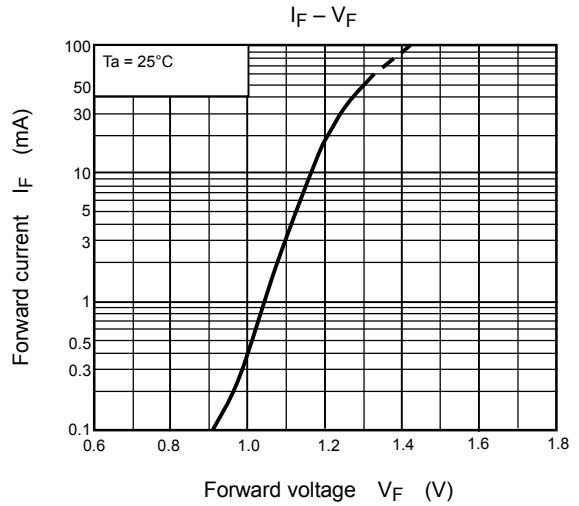
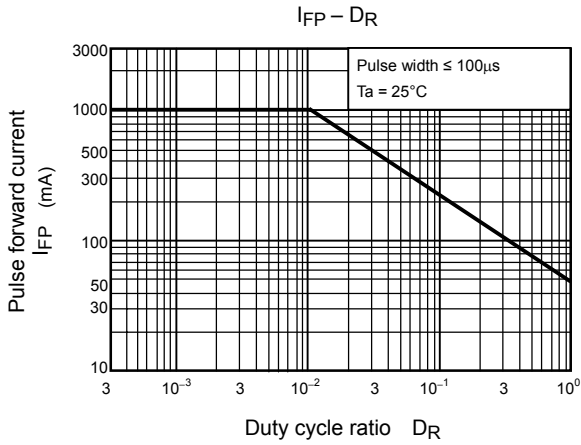
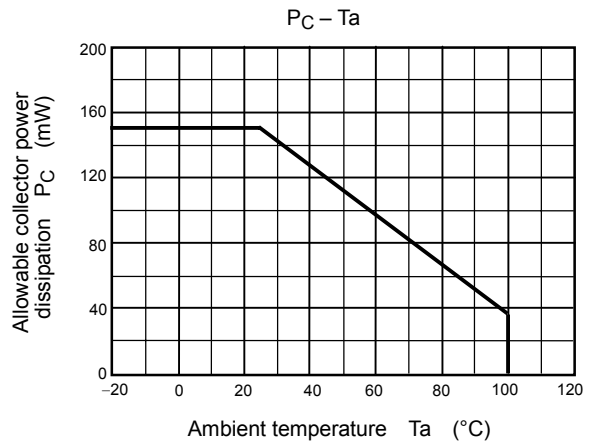
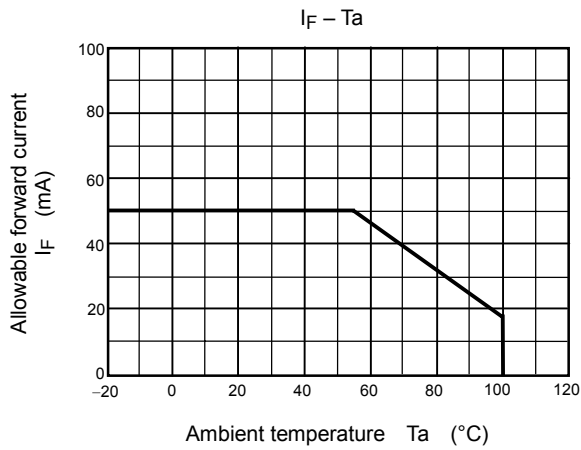
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance input to output	C <sub>S</sub>	V <sub>S</sub> =0, f=1MHz	—	0.8	—	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> =500V	5×10 <sup>10</sup>	10 <sup>14</sup>	—	Ω
Isolation voltage	BV <sub>S</sub>	AC, 1minute	3750	—	—	V <sub>rms</sub>
		AC, 1second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V <sub>dc</sub>

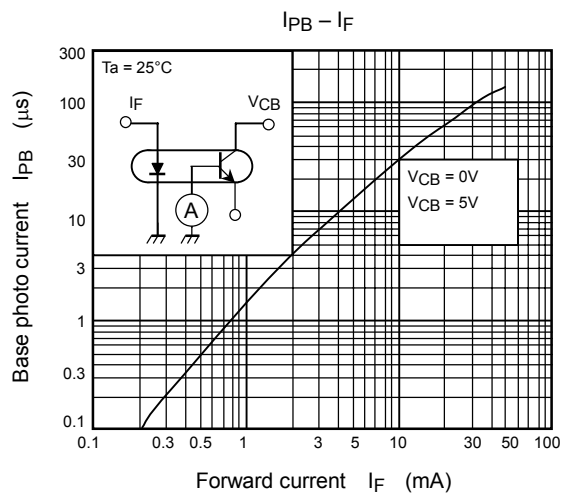
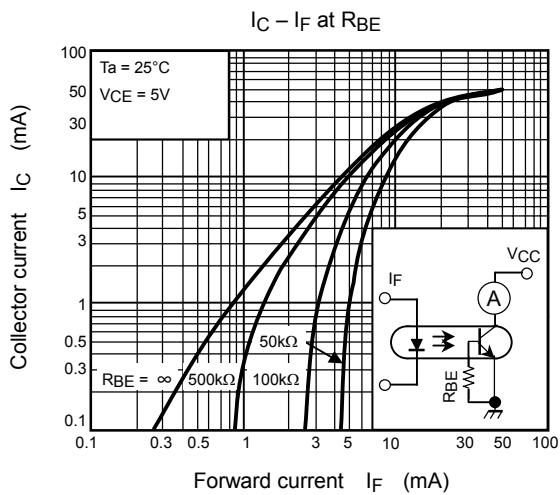
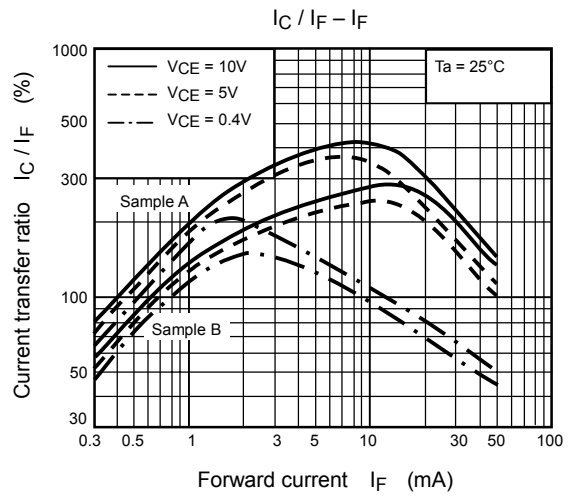
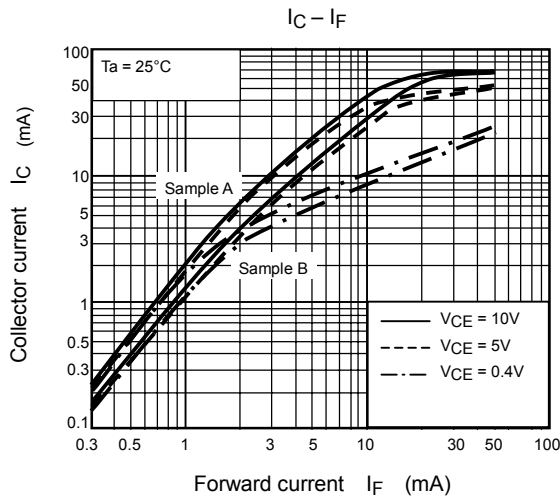
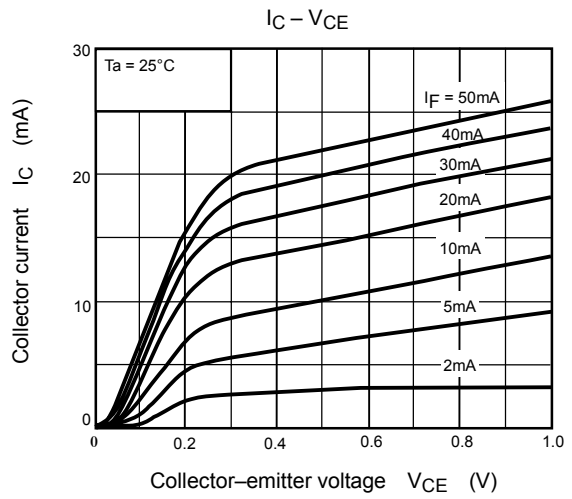
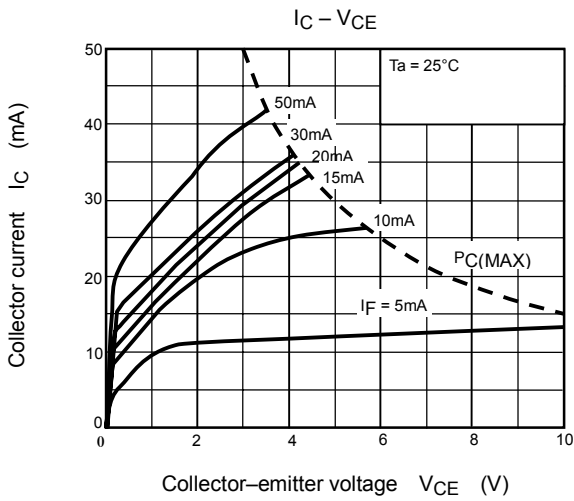
## Switching Characteristics (Ta = 25°C)

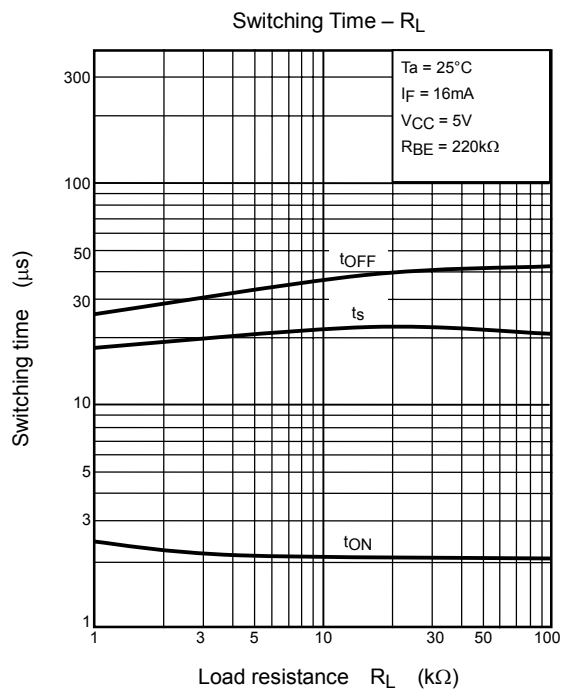
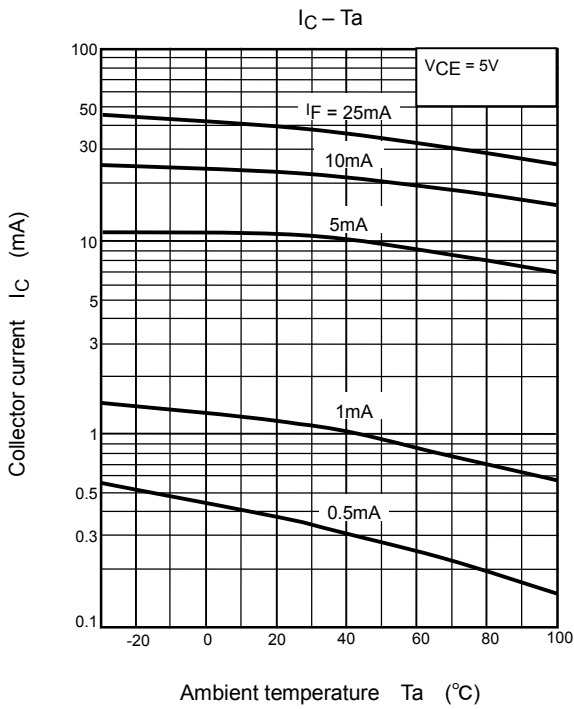
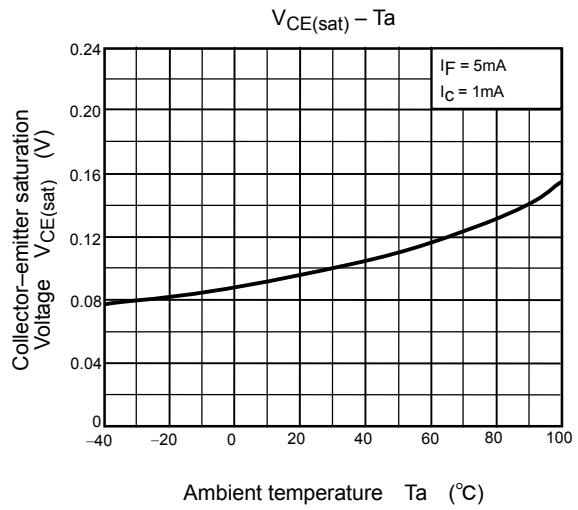
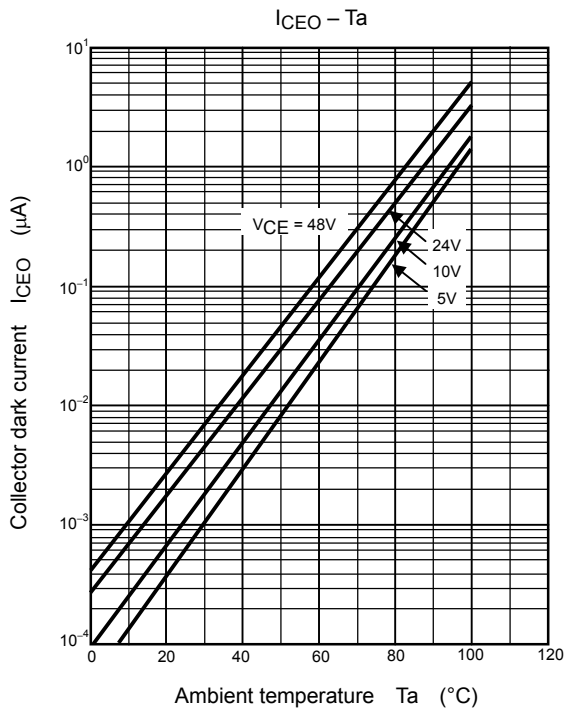
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t <sub>r</sub>	V <sub>CC</sub> = 10V, I <sub>C</sub> = 2mA R <sub>L</sub> = 100Ω	—	2	—	μs
Fall time	t <sub>f</sub>		—	3	—	
Turn-on time	t <sub>on</sub>		—	3	—	
Turn-off time	t <sub>off</sub>		—	3	—	
Turn-on time	t <sub>ON</sub>	R <sub>L</sub> = 1.9 kΩ (Fig.1) R <sub>BE</sub> = OPEN V <sub>CC</sub> = 5 V, I <sub>F</sub> = ±16mA	—	2	—	μs
Storage time	t <sub>S</sub>		—	25	—	
Turn-off time	t <sub>OFF</sub>		—	40	—	
Turn-on time	t <sub>ON</sub>	R <sub>L</sub> = 1.9kΩ (Fig.1) R <sub>BE</sub> = 220kΩ V <sub>CC</sub> = 5 V, I <sub>F</sub> = ±16mA	—	2	—	μs
Storage time	t <sub>S</sub>		—	20	—	
Turn-off time	t <sub>OFF</sub>		—	30	—	

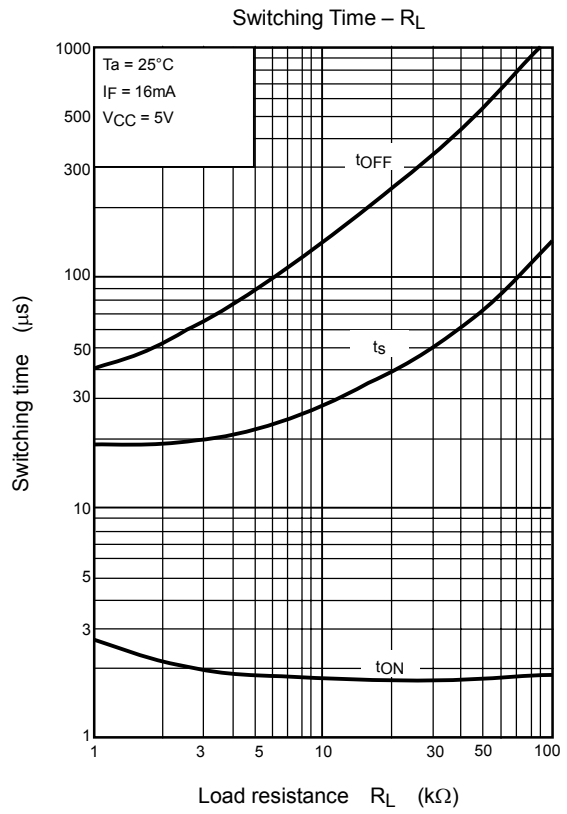
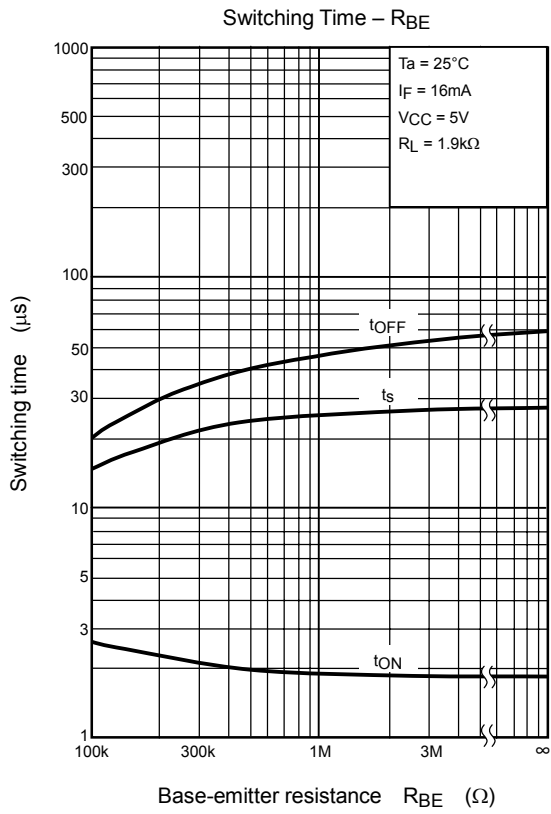
Fig. 1 Switching time test circuit













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